

Product Overview

NSS12100XV6: Low $V_{CE(sat)}$ Transistor, PNP, 12 V, 1.0 A

For complete documentation, see the data sheet.

Low $V_{CE(sat)}$ Bipolar Transistors are miniature surface mount devices featuring ultra low saturation voltage $V_{CE(sat)}$ and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Part Electrical Specifications

Product	Compliance	Status	Polarity	Type	$V_{CE(sat) Max}$ (V)	I_C Cont. (A)	$V_{CE0} Min$ (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(on)}$ (V)	$\beta_{FE} Min$	$\beta_{FE} Max$	f_T Min (MHz)	$P_{TM} Max$ (W)	Package Type
NSS12100XV6T1G	Pb-free	Active	PNP	Low $V_{CE(sat)}$	0.44	1	12	12	5	1.15	1.15	100	-	-	0.65	SOT-563
	Halide free															
NSV12100XV6T1G	AEC Qualified	Active	PNP	Low $V_{CE(sat)}$	0.44	1	12	12	5	1.15	1.15	100	-	-	0.65	SOT-563
	PPAP Capable															
	Pb-free															
	Halide free															

For more information please contact your local sales support at www.onsemi.com.

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